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ON Semiconductor®

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Please note: As part of the Fairchild Semiconductor integration, some of the Fairchild orderable part numbers will need to change in order to meet ON Semiconductor's system requirements. Since the ON Semiconductor product management systems do not have the ability to manage part nomenclature that utilizes an underscore (_), the underscore (_) in the Fairchild part numbers will be changed to a dash (-). This document may contain device numbers with an underscore (_). Please check the ON Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.onsemi.com. Please email any questions regarding the system integration to Fairchild_questions@onsemi.com.

FAIRCHILD SEMICONDUCTOR®

September 2013

FGPF15N60UNDF

600 V, 15 A
Short Circuit Rated IGBT

Features

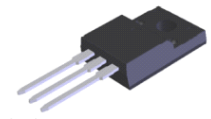
- Short Circuit Rated 10us
- High Current Capability
- High Input Impedance
- Fast Switching
- RoHS Compliant

General Description

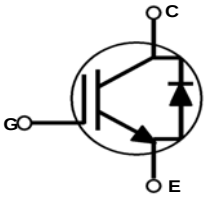
Using advanced NPT IGBT technology, Fairchild's the NPT IGBTs offer the optimum performance for low-power inverter-driven applications where low-losses and short-circuit ruggedness features are essential, such as sewing machine, CNC, motor control and home appliances.

Applications

- Sewing Machine, CNC, Home Appliances, Motor Control



TO-220F
(Retractable)



Absolute Maximum Ratings

Symbol	Description		Ratings	Unit
V_{CES}	Collector to Emitter Voltage		600	V
V_{GES}	Gate to Emitter Voltage		± 20	V
I_C	Collector Current	@ T_C = 25°C	30	A
	Collector Current	@ T_C = 100°C	15	A
$I_{CM\ (1)}$	Pulsed Collector Current	@ T_C = 25°C	45	A
I_F	Diode Forward Current	@ T_C = 25°C	15	A
	Diode Forward Current	@ T_C = 100°C	7.5	A
P_D	Maximum Power Dissipation	@ T_C = 25°C	42	W
	Maximum Power Dissipation	@ T_C = 100°C	17	W
T_J	Operating Junction Temperature		-55 to +150	°C
T_{stg}	Storage Temperature Range		-55 to +150	°C

Notes:
1: Repetitive rating: Pulse width limited by max. junction temperature

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JC}$(IGBT)	Thermal Resistance, Junction to Case	-	3.0	°C/W
$R_{\theta JC}$(Diode)	Thermal Resistance, Junction to Case	-	4.9	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (PCB Mount)(2)	-	62.5	°C/W

Notes:
2: Mountde on 1" square PCB (FR4 or G-10 material)

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FGPF15N60UNDF	FGPF15N60UNDF	TO-220F	-	-	50ea

Electrical Characteristics of the IGBT T_C = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
BV_{CES}	Collector to Emitter Breakdown Voltage	V_{GE} = 0 V, I_C = 250 μA	600	-	-	V
I_{CES}	Collector Cut-Off Current	V_{CE} = V_{CES}, V_{GE} = 0 V	-	-	1	mA
I_{GES}	G-E Leakage Current	V_{GE} = V_{GES}, V_{CE} = 0 V	-	-	±10	μA
On Characteristics						
$V_{GE(th)}$	G-E Threshold Voltage	I_C = 15 mA, V_{CE} = V_{GE}	5.5	6.8	8.5	V
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	I_C = 15 A, V_{GE} = 15 V	-	2.2	2.7	V
		I_C = 15 A, V_{GE} = 15 V, T_C = 125°C	-	2.7	-	V
Dynamic Characteristics						
C_{ies}	Input Capacitance	V_{CE} = 30 V, V_{GE} = 0 V, f = 1MHz	-	619	-	pF
C_{oes}	Output Capacitance		-	80	-	pF
C_{res}	Reverse Transfer Capacitance		-	24	-	pF
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{CC} = 400 V, I_C = 15 A, R_G = 10 Ω, V_{GE} = 15 V, Inductive Load, T_C = 25°C	-	9.3	-	ns
t_r	Rise Time		-	9.8	-	ns
$t_{d(off)}$	Turn-Off Delay Time		-	54.8	-	ns
t_f	Fall Time		-	9.9	12.8	ns
E_{on}	Turn-On Switching Loss		-	0.37	-	mJ
E_{off}	Turn-Off Switching Loss		-	0.067	-	mJ
E_{ts}	Total Switching Loss		-	0.44	-	mJ
$t_{d(on)}$	Turn-On Delay Time	V_{CC} = 400 V, I_C = 15 A, R_G = 10 Ω, V_{GE} = 15 V, Inductive Load, T_C = 125°C	-	8.9	-	ns
t_r	Rise Time		-	9.9	-	ns
$t_{d(off)}$	Turn-Off Delay Time		-	56.6	-	ns
t_f	Fall Time		-	13.2	-	ns
E_{on}	Turn-On Switching Loss		-	0.54	-	mJ
E_{off}	Turn-Off Switching Loss		-	0.11	-	mJ
E_{ts}	Total Switching Loss		-	0.65	-	mJ
T_{sc}	Short Circuit Withstand Time	V_{CC} = 350 V, R_G = 100 Ω, V_{GE} = 15 V, T_C = 150°C	10	-	-	μs

Electrical Characteristics of the IGBT T_C = 25°C unless otherwise noted

Q_g	Total Gate Charge	V_{CE} = 400 V, I_C = 15 A, V_{GE} = 15 V	-	43	-	nC
Q_{ge}	Gate to Emitter Charge		-	6	-	nC
Q_{gc}	Gate to Collector Charge		-	26	-	nC

Electrical Characteristics of the Diode T_C = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions		Min.	Typ.	Max	Unit
V_{FM}	Diode Forward Voltage	I_F = 15 A	T_C = 25°C	-	1.6	2.2	V
			T_C= 125°C	-	1.5	-	
t_{rr}	Diode Reverse Recovery Time	I_F =15 A, dI_F/dt = 200 A/µs	T_C = 25°C	-	82.4		ns
			T_C= 125°C	-	142	-	
Q_{rr}	Diode Reverse Recovery Charge		T_C = 25°C	-	213	-	nC
			T_C= 125°C	-	541	-	

Typical Performance Characteristics

Figure 1. Typical Output Characteristics

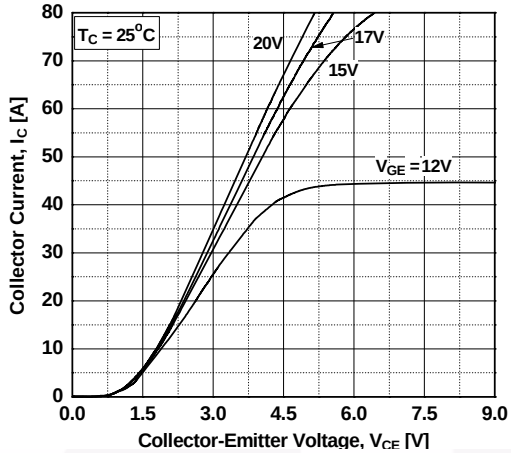


Figure 2. Typical Output Characteristics

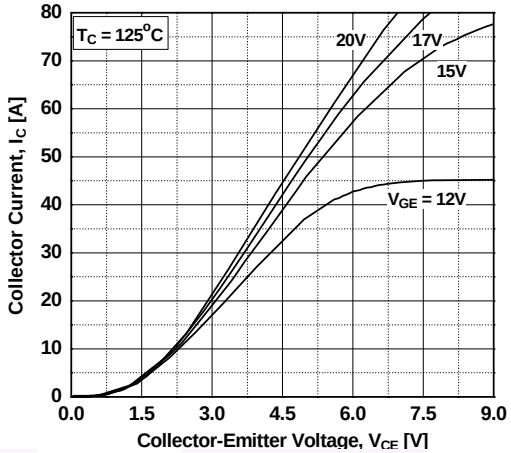


Figure 3. Typical Saturation Voltage Characteristics

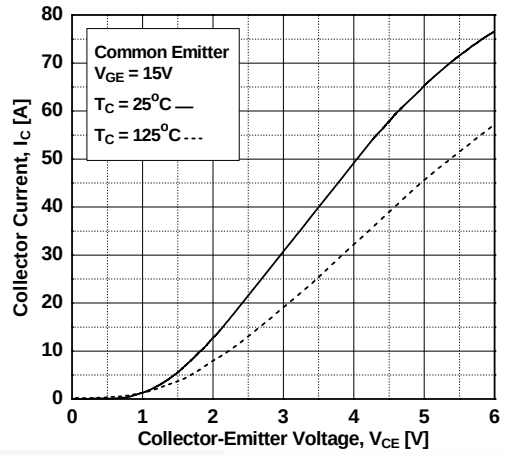


Figure 4. Transfer Characteristics

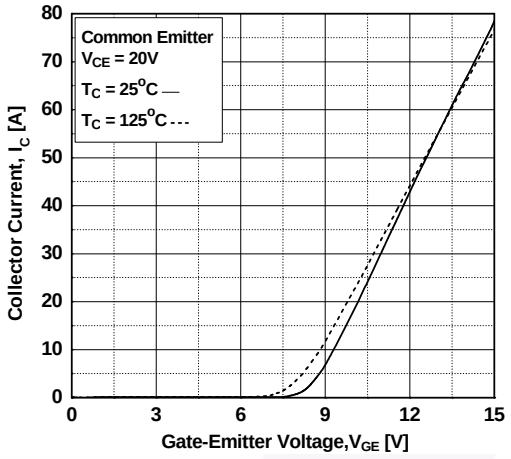


Figure 5. Saturation Voltage vs. Case Temperature at Variant Current Level

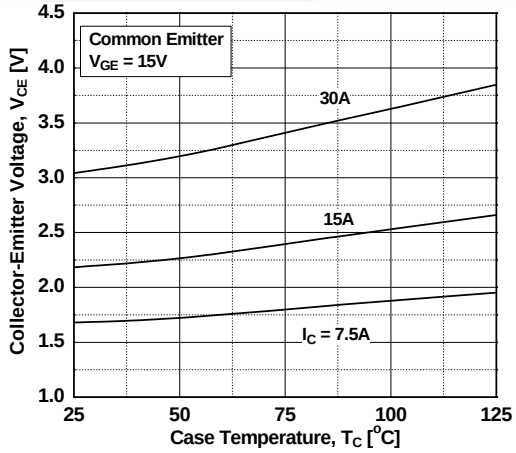
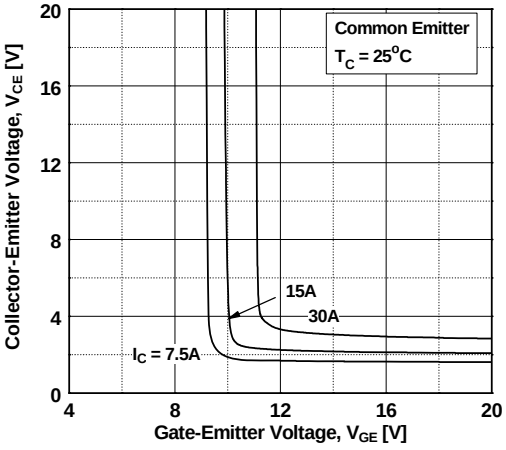


Figure 6. Saturation Voltage vs. V_{GE}



Typical Performance Characteristics

Figure 7. Saturation Voltage vs. V_{GE}

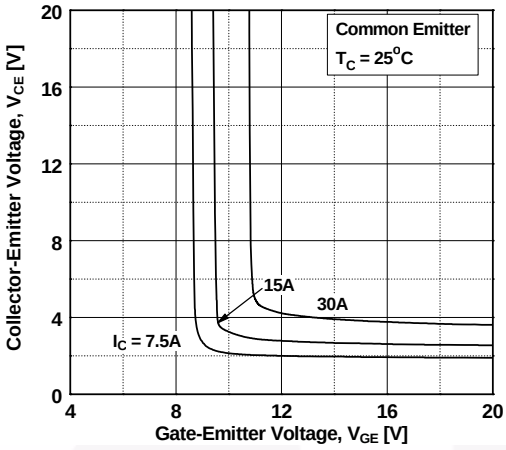


Figure 8. Capacitance Characteristics

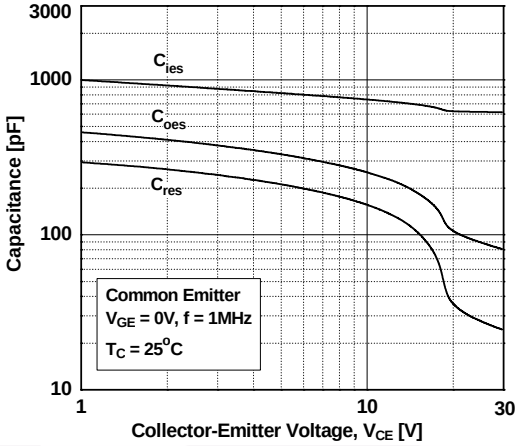


Figure 9. Gate charge Characteristics

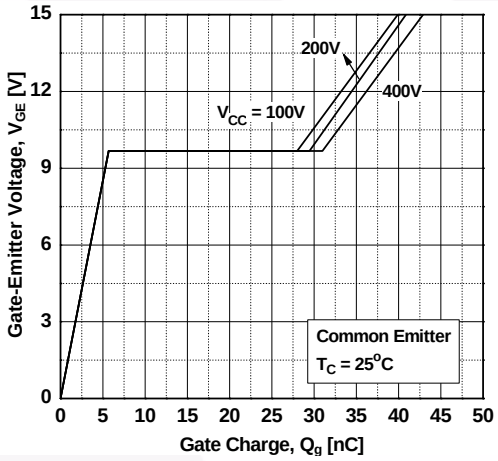


Figure 10. SOA Characteristics

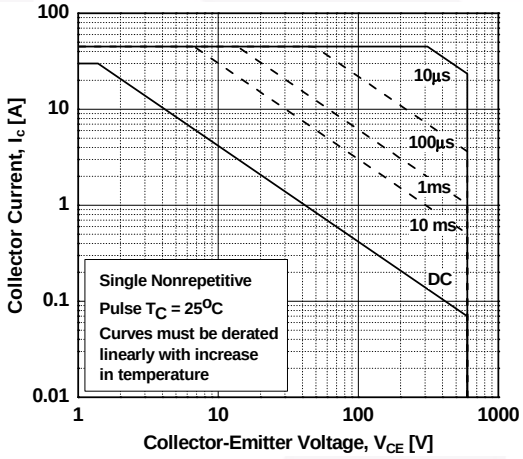


Figure 11. Turn-on Characteristics vs. Gate Resistance

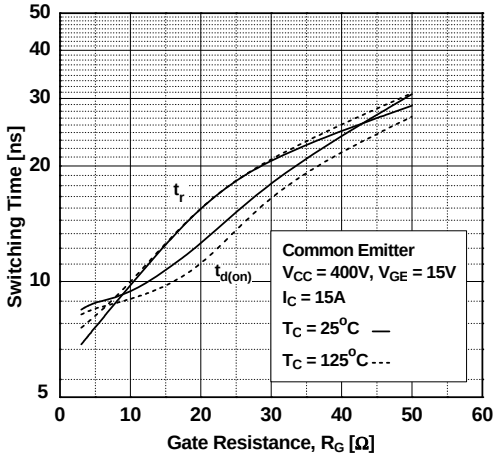
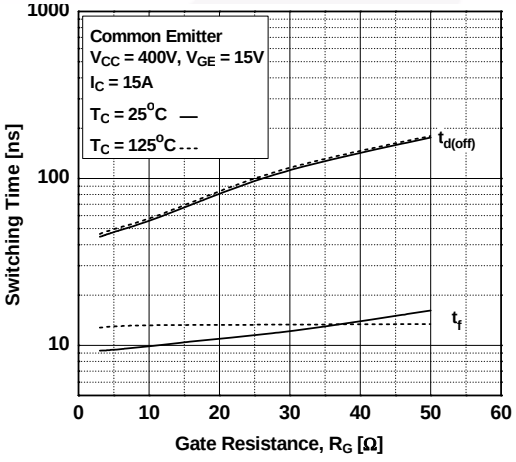


Figure 12. Turn-off Characteristics vs. Gate Resistance



Typical Performance Characteristics

Figure 13. Turn-on Characteristics vs. Collector Current

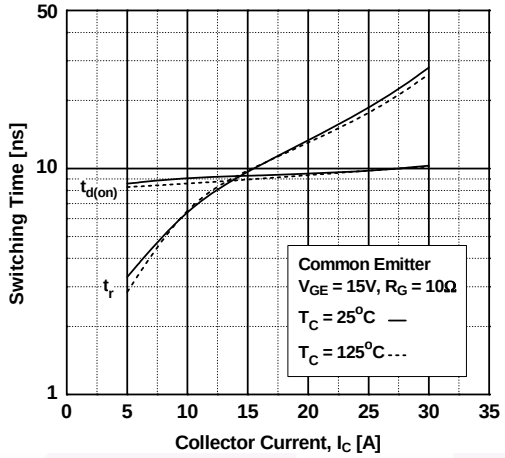


Figure 14. Turn-off Characteristics vs. Collector Current

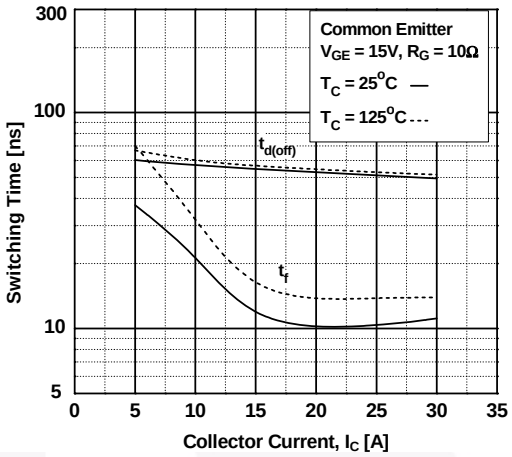


Figure 15. Switching Loss vs. Gate Resistance

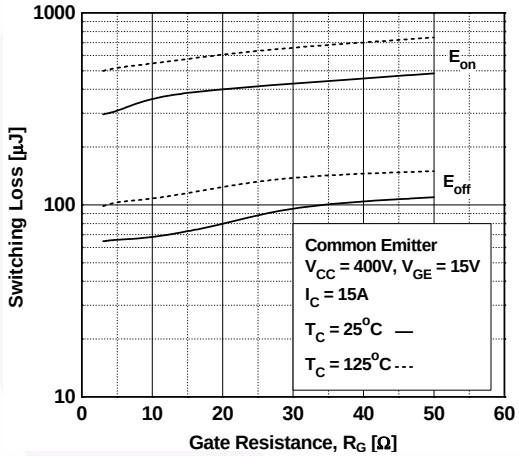


Figure 16. Switching Loss vs Collector Current

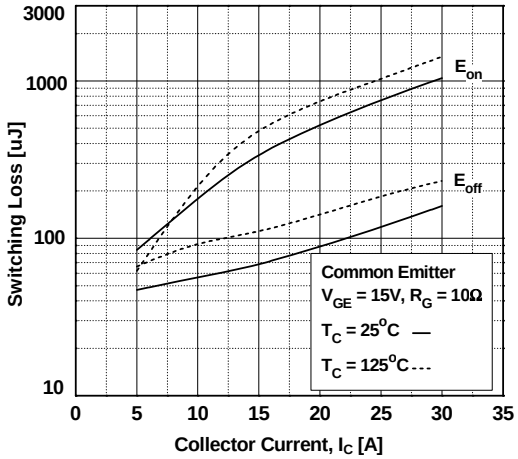


Figure 17. Turn off Switching SOA Characteristics

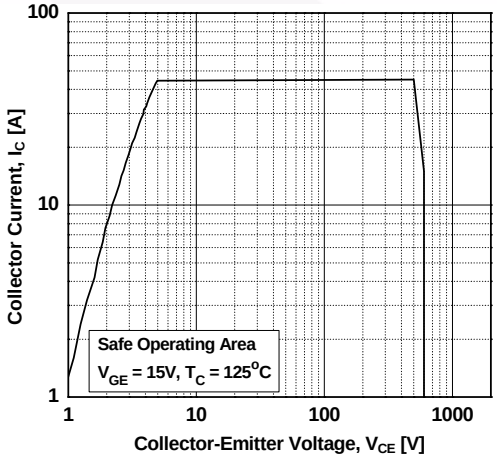
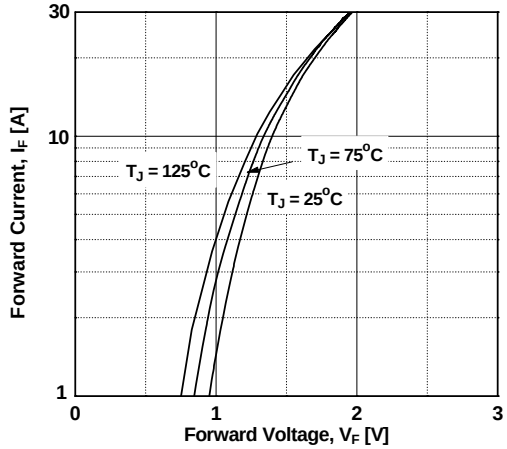


Figure 18. Forward Characteristics



Typical Performance Characteristics

Figure 19. Reverse Current

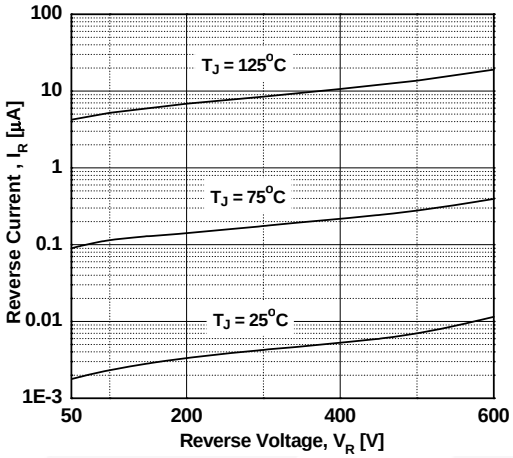


Figure 20. Stored Charge

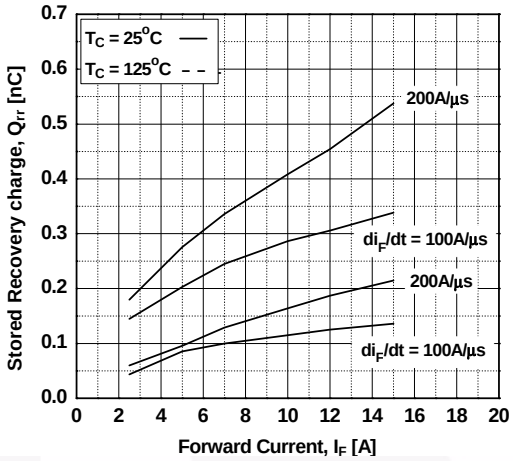


Figure 21. Reverse Recovery Time

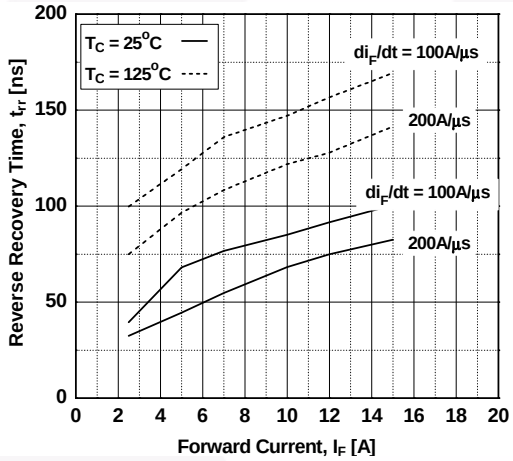
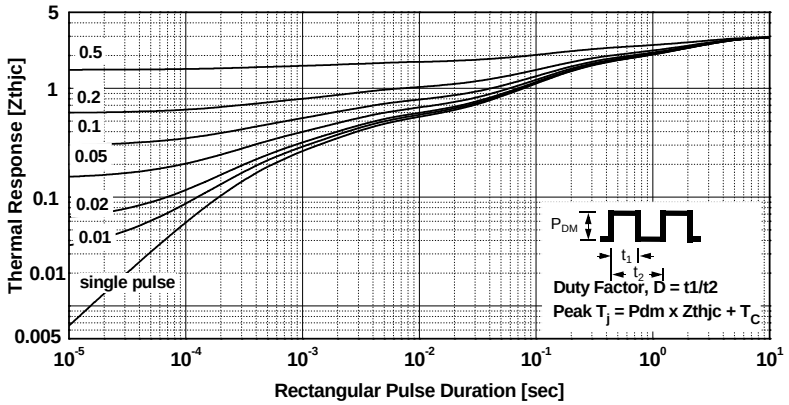


Figure 22.Transient Thermal Impedance of IGBT



Mechanical Dimensions

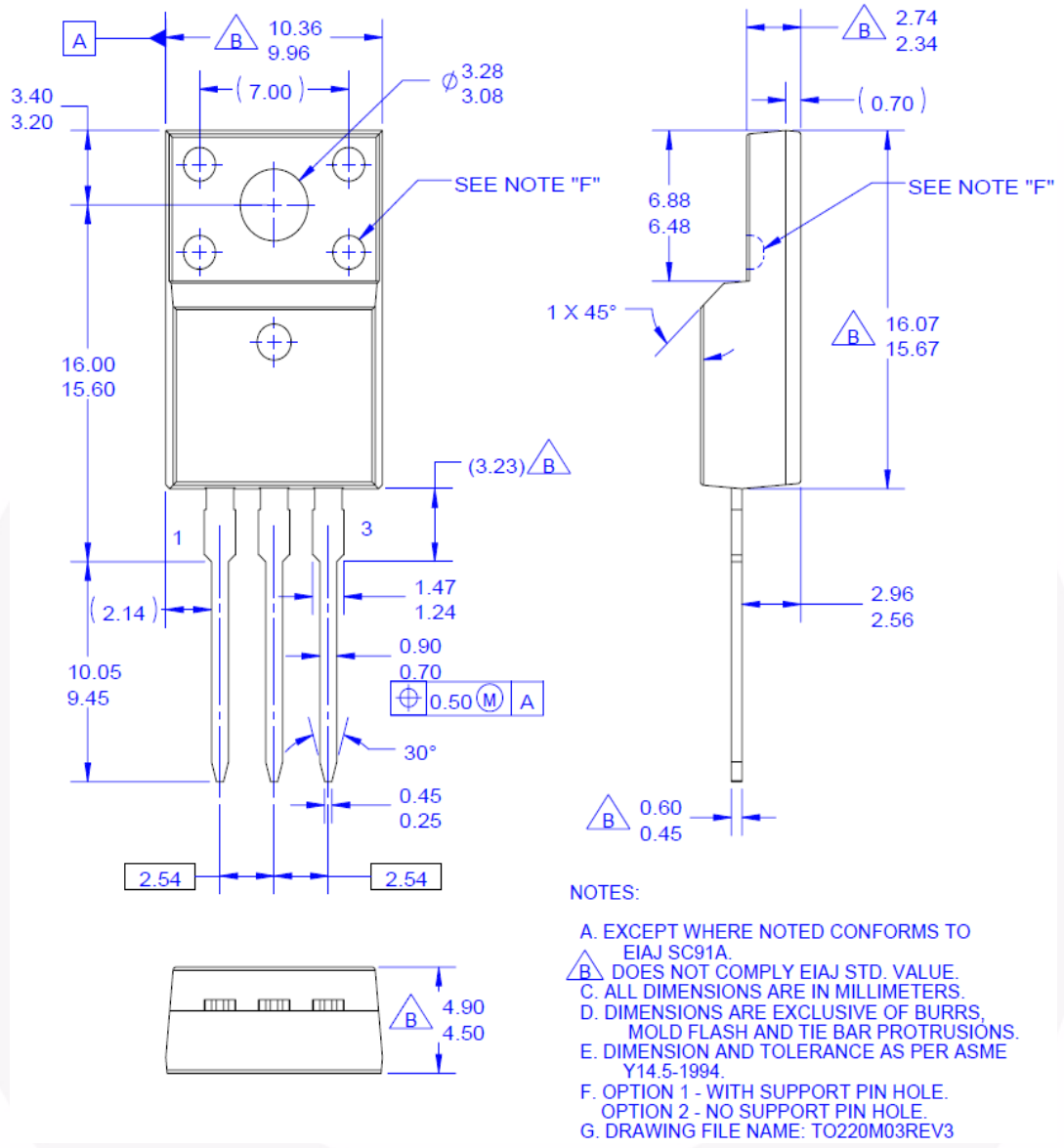


Figure 23. TO-220F 3L - TO220, MOLDED, 3LD, FULL PACK, EIAJ SC91, STRAIGHT LEAD

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Dimensions in Millimeters

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PRODUCT STATUS DEFINITIONS
Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative / In Design	Datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
Obsolete	Not In Production	Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.

Rev. I66

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